VHF/UHF Transistor

NPN Silicon

Features

 These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	3.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

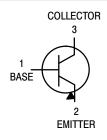
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina



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SOT-23 (TO-236AB) CASE 318 STYLE 6

MARKING DIAGRAMS





MMBTH10LT1G

MMBTH10-04LT1G

3EM, 3E4 = Specific Device Code

M = Date Code* ■ Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTH10LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
MMBTH10LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel
MMBTH10-4LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•	•	
Collector–Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	25	_	_	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	V _{(BR)CBO}	30	-	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	3.0	-	-	Vdc
Collector Cutoff Current (V _{CB} = 25 Vdc, I _E = 0)	I _{CBO}	_	-	100	nAdc
Emitter Cutoff Current (V _{EB} = 2.0 Vdc, I _C = 0)	I _{EBO}	_	-	100	nAdc
ON CHARACTERISTICS					
DC Current Gain $(I_C = 4.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ \text{MMBTH10L} \\ \text{MMBTH10-4L} \\ $		60 120	- -	_ 240	_
Collector–Emitter Saturation Voltage (I _C = 4.0 mAdc, I _B = 0.4 mAdc)	V _{CE(sat)}	-	-	0.5	Vdc
Base-Emitter On Voltage (I _C = 4.0 mAdc, V _{CE} = 10 Vdc)	V _{BE}	-	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS			•	•	
Current-Gain - Bandwidth Product (I _C = 4.0 mAdc, V _{CE} = 10 Vdc, f = 100 MHz) MMBTH10L ⁻ MMBTH10-4L ⁻	•	650 800	- -	- -	MHz
Collector-Base Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	-	-	0.7	pF
Common-Base Feedback Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{rb}	-	-	0.65	pF
Collector Base Time Constant (I _C = 4.0 mAdc, V _{CB} = 10 Vdc, f = 31.8 MHz)	rb′C _c	-	-	9.0	ps

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

 $(V_{CB} = 10 \text{ Vdc}, I_C = 4.0 \text{ mAdc}, T_A = 25^{\circ}\text{C})$

y_{ib}, INPUT ADMITTANCE

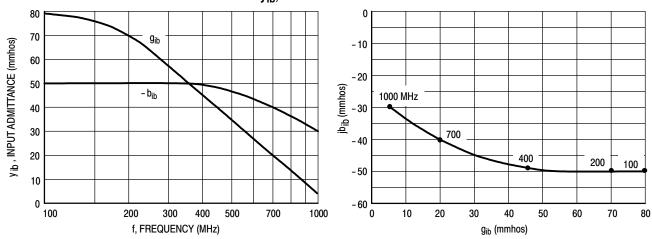


Figure 1. Rectangular Form

Figure 2. Polar Form

y_{fb}, FORWARD TRANSFER ADMITTANCE

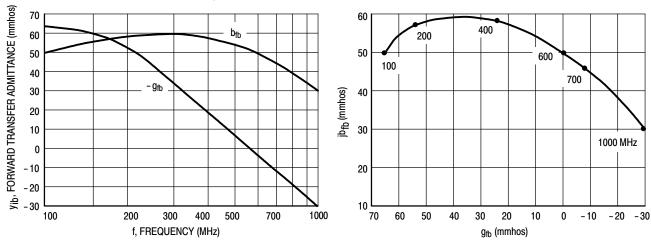


Figure 3. Rectangular Form

Figure 4. Polar Form

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

 $(V_{CB} = 10 \text{ Vdc}, I_C = 4.0 \text{ mAdc}, T_A = 25^{\circ}\text{C})$

y_{rb}, REVERSE TRANSFER ADMITTANCE

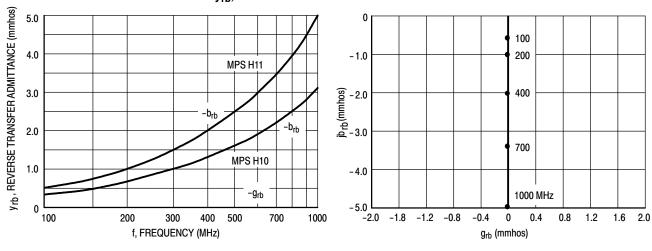


Figure 5. Rectangular Form

Figure 6. Polar Form

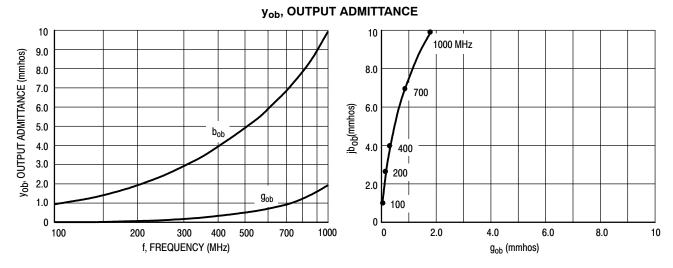
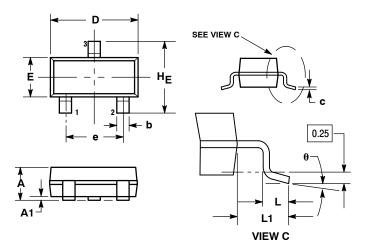


Figure 7. Rectangular Form

Figure 8. Polar Form

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD
- 318-08.

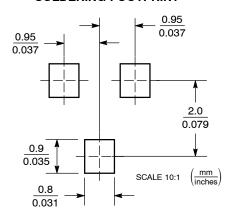
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

PIN 1. BASE 2. EMITTER

- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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